

Notice of References Cited

Application/Control No.

09/103,873

Applicant(s)/Patent Under

Reexamination

NAGANO ET AL.

Examiner

José R. Diaz

Art Unit

2815

Page 1 of 1

U.S. PATENT DOCUMENTS

*		DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	DOCUMENT SOURCE **	
							APS	OTHER
<input type="checkbox"/>	A	5,608,251	Mar. 1997	Konuma et al.	257	337	<input checked="" type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	B	5,459,353	Oct. 1995	Kanazawa	257	751	<input checked="" type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	C	5,789,762	Aug. 1998	Koyama et al	257	66	<input checked="" type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	D	5,990,507	Nov. 1999	Mochizuki et al.	257	295	<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	E						<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	F						<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	G						<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	H						<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	I						<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	J						<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	K						<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	L						<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	M						<input type="checkbox"/>	<input type="checkbox"/>

FOREIGN PATENT DOCUMENTS

*		DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS	DOCUMENT SOURCE **	
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<input type="checkbox"/>	N							<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	O							<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	P							<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	Q							<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	R							<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	S							<input type="checkbox"/>	<input type="checkbox"/>
<input type="checkbox"/>	T							<input type="checkbox"/>	<input type="checkbox"/>

NON-PATENT DOCUMENTS

*		DOCUMENT (Including Author, Title Date, Source, and Pertinent Pages)	DOCUMENT SOURCE **	
			APS	OTHER
<input type="checkbox"/>	U	K. Fujino et al., "Reaction Mechanism of TEOS and O3 Atmospheric Pressure, IEEE Conference, 1991, pp 445-447.	<input type="checkbox"/>	<input type="checkbox"/>
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*A copy of this reference is not being furnished with this Office action. (See Manual of Patent Examining Procedure, Section 707.05(a).)

**APS encompasses any electronic search i.e. text, image, and Commercial Databases.

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